

# HD74HC670

## 4-by-4 Register File (with 3-state outputs)

REJ03D0639-0200  
 (Previous ADE-205-521)  
 Rev.2.00  
 Mar 30, 2006

### Description

The HD74HC670, 16-bit register file is organized as 4 words of 4 bits each and separate on-chip decoding is provided for addressing the four word locations to either write-in or retrieve data.

This permits simultaneous writing into one location and reading from another word location. Four data inputs are available which are used to supply the 4-bit word to be stored. Location of the word is determined by the write-address inputs A and B in conjunction with a write-enable signal. Data applied at the inputs should be in its true form. That is, if a high-level signal is desired from the output, a high-level is applied at the data input for that particular bit location. The latch inputs are arranged so that new data will be accepted only if both internal address gate inputs are high. When this condition exists, data at the D input is transferred to the latch output. When the write-enable input, ( $G_W$ ) is high, the data inputs are inhibited and their levels can cause no change in the information stored in the internal latches. When the read-enable input, ( $G_R$ ) is high, the data outputs are inhibited and go into the high-impedance state. The individual address lines permit direct acquisition of data stored in any four of the latches. Four individual decoding gates are used to complete the address for reading a word. When the read address is made in conjunction with the read-enable signal, the word appears at the four outputs.

### Features

- High Speed Operation:  $t_{pd}$  (Read Select to Q) = 21 ns typ ( $C_L = 50$  pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage:  $V_{CC} = 2$  to 6 V
- Low Input Current: 1  $\mu$ A max
- Low Quiescent Supply Current:  $I_{CC}$  (static) = 4  $\mu$ A max ( $T_a = 25^\circ\text{C}$ )
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC670P	DILP-16 pin	PRDP0016AE-B (DP-16FV)	P	—
HD74HC670FPEL	SOP-16 pin (JEITA)	PRSP0016DH-B (FP-16DAV)	FP	EL (2,000 pcs/reel)

Note: Please consult the sales office for the above package availability.

### Function Table

Write Inputs			Word			
$W_B$	$W_A$	$G_W$	0	1	2	3
L	L	L	$Q = D$	$Q_0$	$Q_0$	$Q_0$
L	H	L	$Q_0$	$Q = D$	$Q_0$	$Q_0$
H	L	L	$Q_0$	$Q_0$	$Q = D$	$Q_0$
H	H	L	$Q_0$	$Q_0$	$Q_0$	$Q = D$
X	X	H	$Q_0$	$Q_0$	$Q_0$	$Q_0$

Read Inputs			Outputs			
$R_B$	$R_A$	$G_R$	$Q_1$	$Q_2$	$Q_3$	$Q_4$
L	L	L	$W_0 B_1$	$W_0 B_2$	$W_0 B_3$	$W_0 B_4$
L	H	L	$W_1 B_1$	$W_1 B_2$	$W_1 B_3$	$W_1 B_4$
H	L	L	$W_2 B_1$	$W_2 B_2$	$W_2 B_3$	$W_2 B_4$
H	H	L	$W_3 B_1$	$W_3 B_2$	$W_3 B_3$	$W_3 B_4$
X	X	H	Z	Z	Z	Z

H : high level

L : low level

X : irrelevant

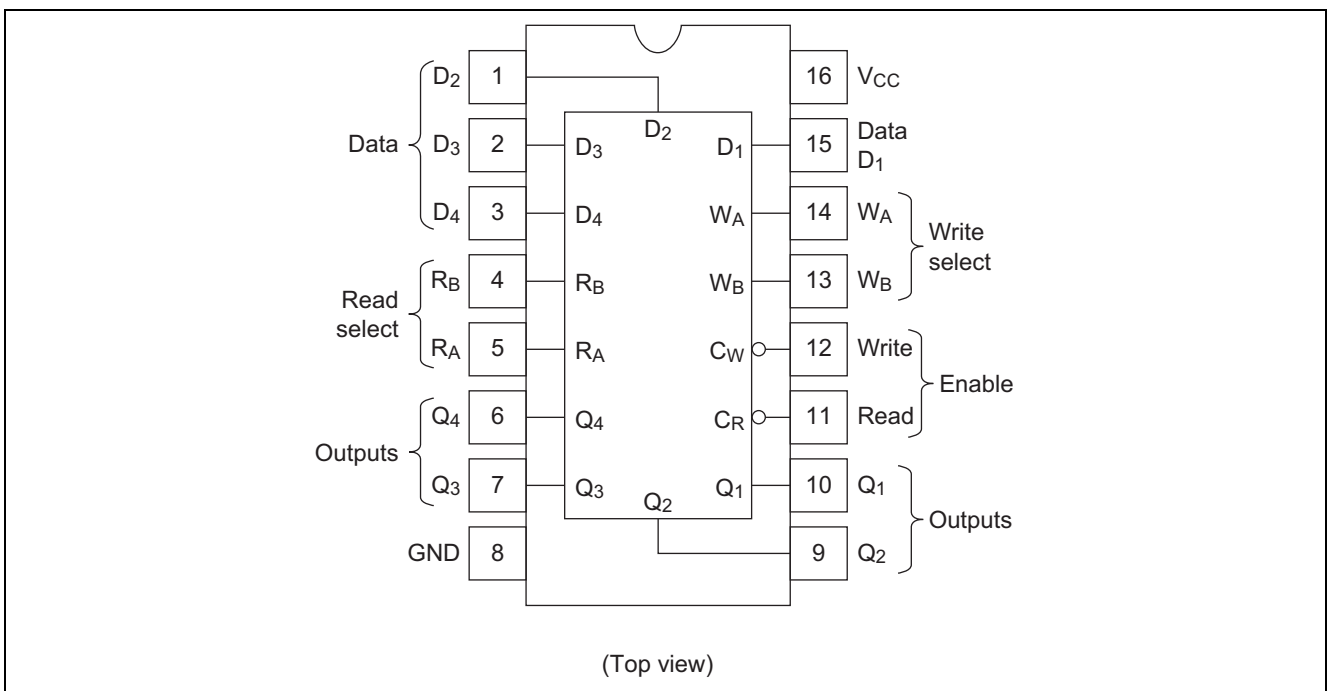
Z : high impedance (off)

( $Q = D$ ): The four selected internal flip-flop outputs will assume the states applied to the four external data inputs.

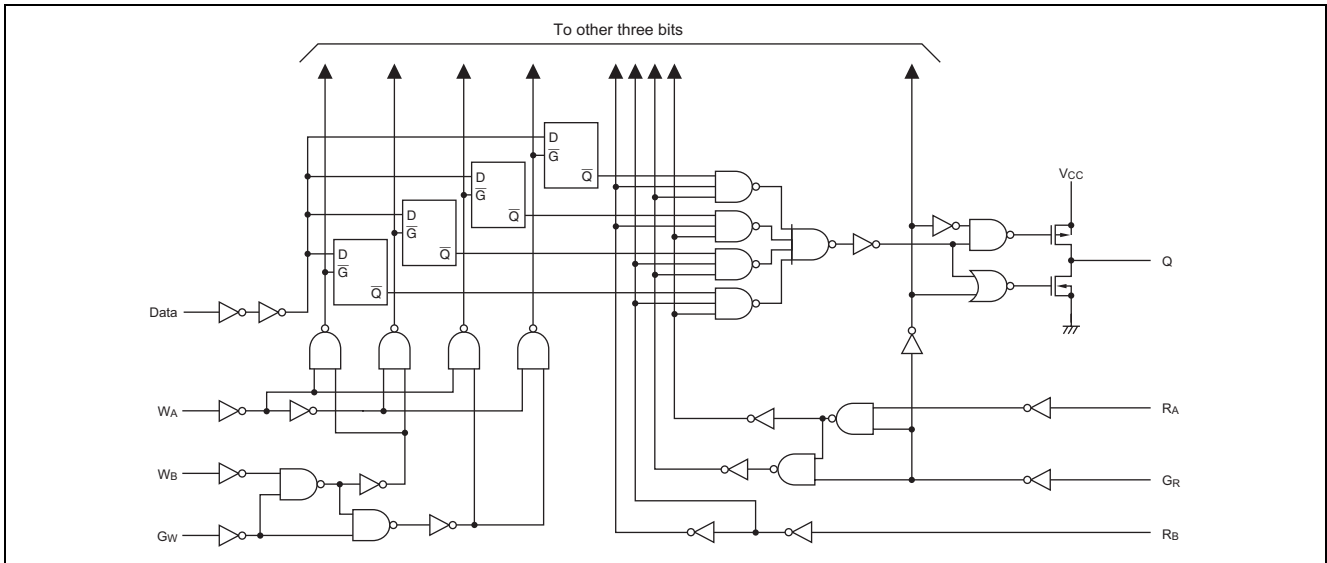
$Q_0$  : The level of Q before the indicated input conditions were established.

$W_0 B_1$  : The first bit of word 0, etc.

### Pin Arrangement



Logic Diagram



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Supply voltage range	$V_{CC}$	-0.5 to 7.0	V
Input / Output voltage	$V_{IN}, V_{OUT}$	-0.5 to $V_{CC} + 0.5$	V
Input / Output diode current	$I_{IK}, I_{OK}$	$\pm 20$	mA
Output current	$I_{OUT}$	$\pm 35$	mA
$V_{CC}$ , GND current	$I_{CC}$ or $I_{GND}$	$\pm 75$	mA
Power dissipation	$P_T$	500	mW
Storage temperature	$T_{stg}$	-65 to +150	$^{\circ}C$

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	$V_{CC}$	2 to 6	V	
Input / Output voltage	$V_{IN}, V_{OUT}$	0 to $V_{CC}$	V	
Operating temperature	$T_a$	-40 to 85	$^{\circ}C$	
Input rise / fall time*1	$t_r, t_f$	0 to 1000	ns	$V_{CC} = 2.0 V$
		0 to 500		$V_{CC} = 4.5 V$
		0 to 400		$V_{CC} = 6.0 V$

Note: 1. This item guarantees maximum limit when one input switches.  
 Waveform: Refer to test circuit of switching characteristics.

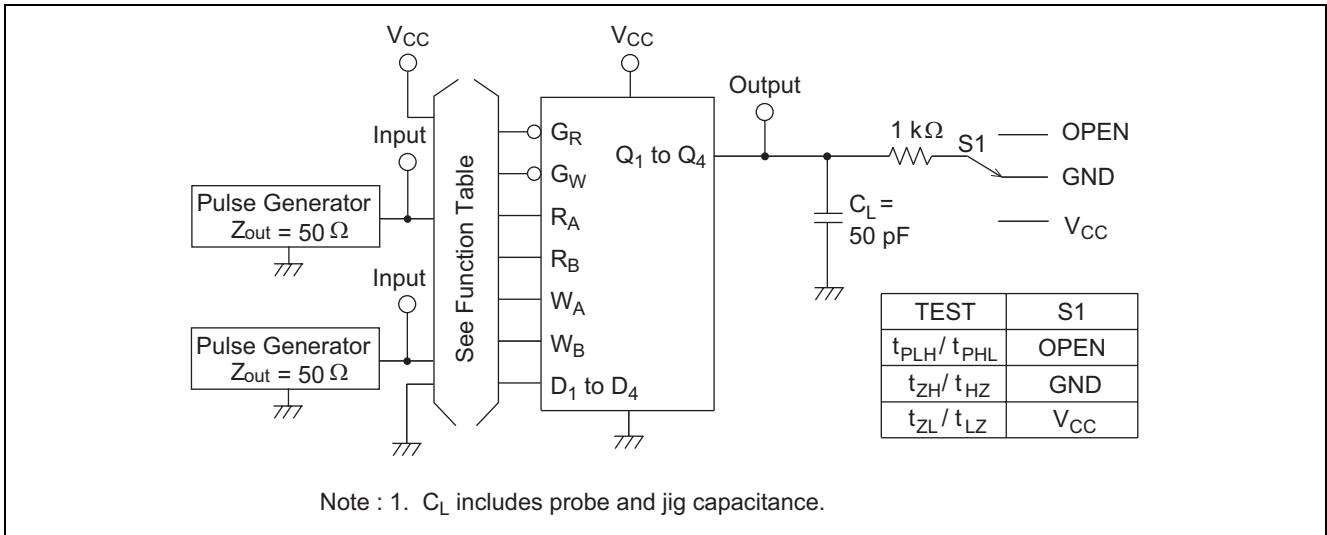
**Electrical Characteristics**

Item	Symbol	V <sub>CC</sub> (V)	Ta = 25°C			Ta = -40 to+85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Input voltage	V <sub>IH</sub>	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V <sub>IL</sub>	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V <sub>OH</sub>	2.0	1.9	2.0	—	1.9	—	V	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -20 μA
		4.5	4.4	4.5	—	4.4	—			I <sub>OH</sub> = -6 mA
		6.0	5.9	6.0	—	5.9	—			I <sub>OH</sub> = -7.8 mA
		4.5	4.18	—	—	4.13	—			
		6.0	5.68	—	—	5.63	—			
	V <sub>OL</sub>	2.0	—	0.0	0.1	—	0.1	V	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 20 μA
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			I <sub>OL</sub> = 6 mA
		6.0	—	—	0.26	—	0.33			I <sub>OL</sub> = 7.8 mA
Off-state output current	I <sub>oz</sub>	6.0	—	—	±0.5	—	±5.0	μA	V <sub>in</sub> = V <sub>IN</sub> or V <sub>IL</sub> , V <sub>out</sub> = V <sub>CC</sub> or GND	
Input current	I <sub>in</sub>	6.0	—	—	±0.1	—	±1.0	μA	V <sub>in</sub> = V <sub>CC</sub> or GND	
Quiescent supply current	I <sub>CC</sub>	6.0	—	—	4.0	—	40	μA	V <sub>in</sub> = V <sub>CC</sub> or GND, I <sub>out</sub> = 0 μA	

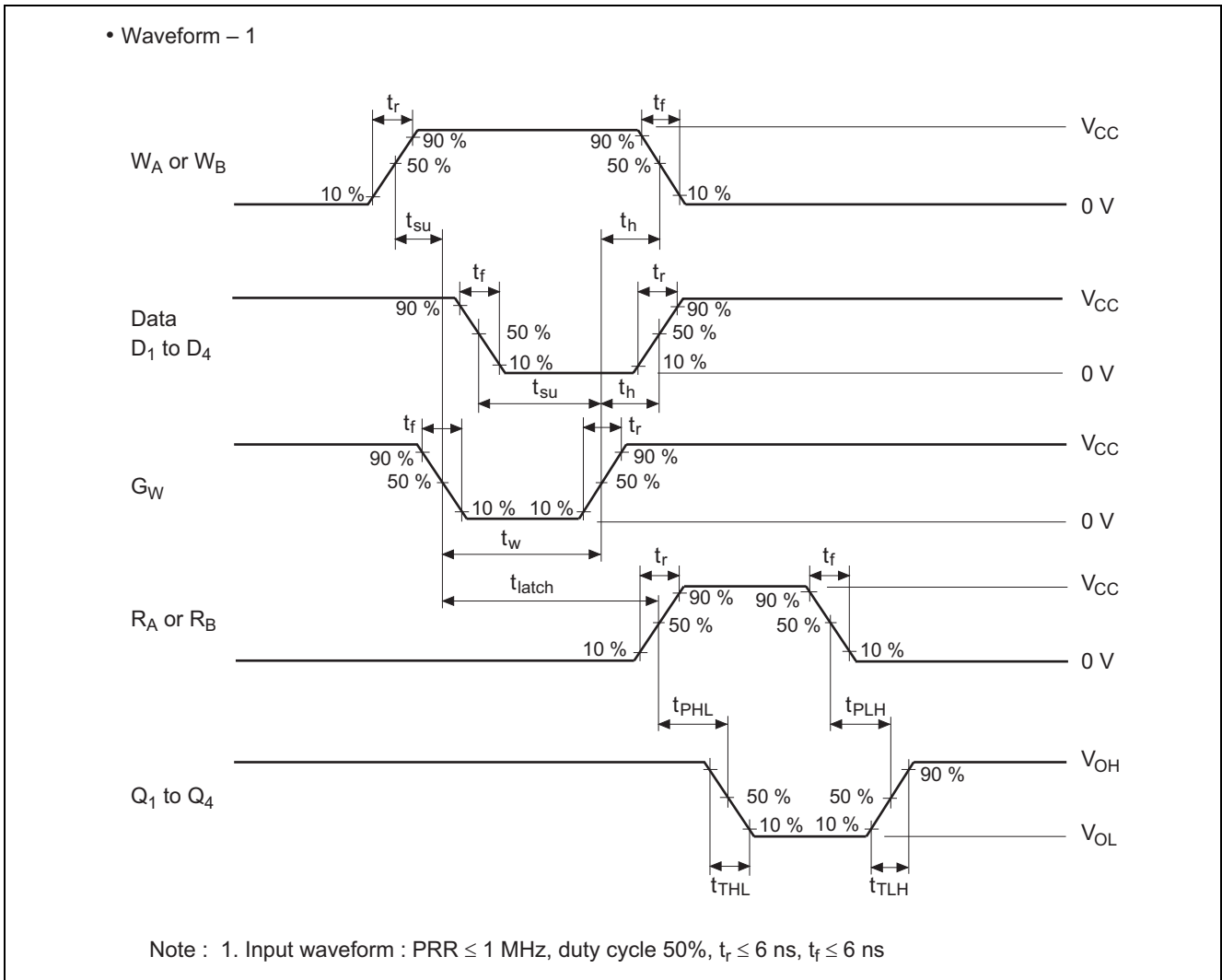
Switching Characteristics ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6 \text{ ns}$ )

Item	Symbol	$V_{CC}$ (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \text{ to } +85^\circ\text{C}$		Unit	Test Conditions
			Min	Typ	Max	Min	Max		
Propagation delay time	$t_{PLH}$	2.0	—	—	160	—	200	ns	Read select to Q
		4.5	—	21	32	—	40		
		6.0	—	—	27	—	34		
	$t_{PHL}$	2.0	—	—	200	—	250	ns	Write enable to Q
		4.5	—	24	40	—	50		
		6.0	—	—	34	—	43		
	$t_{PLH}$	2.0	—	—	150	—	190	ns	Data to Q
		4.5	—	18	30	—	38		
		6.0	—	—	26	—	33		
Output enable time	$t_{ZH}$	2.0	—	—	150	—	190	ns	
		4.5	—	18	30	—	38		
		6.0	—	—	26	—	33		
Output disable time	$t_{LZ}$	2.0	—	—	150	—	190	ns	
		4.5	—	17	30	—	38		
		6.0	—	—	26	—	33		
Pulse width	$t_w$	2.0	80	—	—	100	—	ns	
		4.5	16	—	—	20	—		
		6.0	14	—	—	17	—		
Setup time	$t_{su}$	2.0	60	—	—	75	—	ns	Data to Write enable
		4.5	12	4	—	15	—		
		6.0	10	—	—	13	—		
		2.0	60	—	—	75	—	ns	Write select to Write enable
		4.5	12	—	—	15	—		
		6.0	10	—	—	13	—		
Hold time	$t_h$	2.0	50	—	—	63	—	ns	Write enable to Data
		4.5	10	6	—	13	—		
		6.0	9	—	—	11	—		
		2.0	50	—	—	63	—	ns	Write enable to Write select
		4.5	10	—	—	13	—		
		6.0	9	—	—	11	—		
Latch time for new data	$t_{latch}$	2.5	100	—	—	125	—	ns	
		4.5	20	—	—	25	—		
		6.0	17	—	—	21	—		
Output rise/fall time	$t_{TLH}$	2.0	—	—	75	—	95	ns	
		4.5	—	5	15	—	19		
		6.0	—	—	13	—	16		
Input capacitance	$C_{in}$	—	—	5	10	—	10	pF	

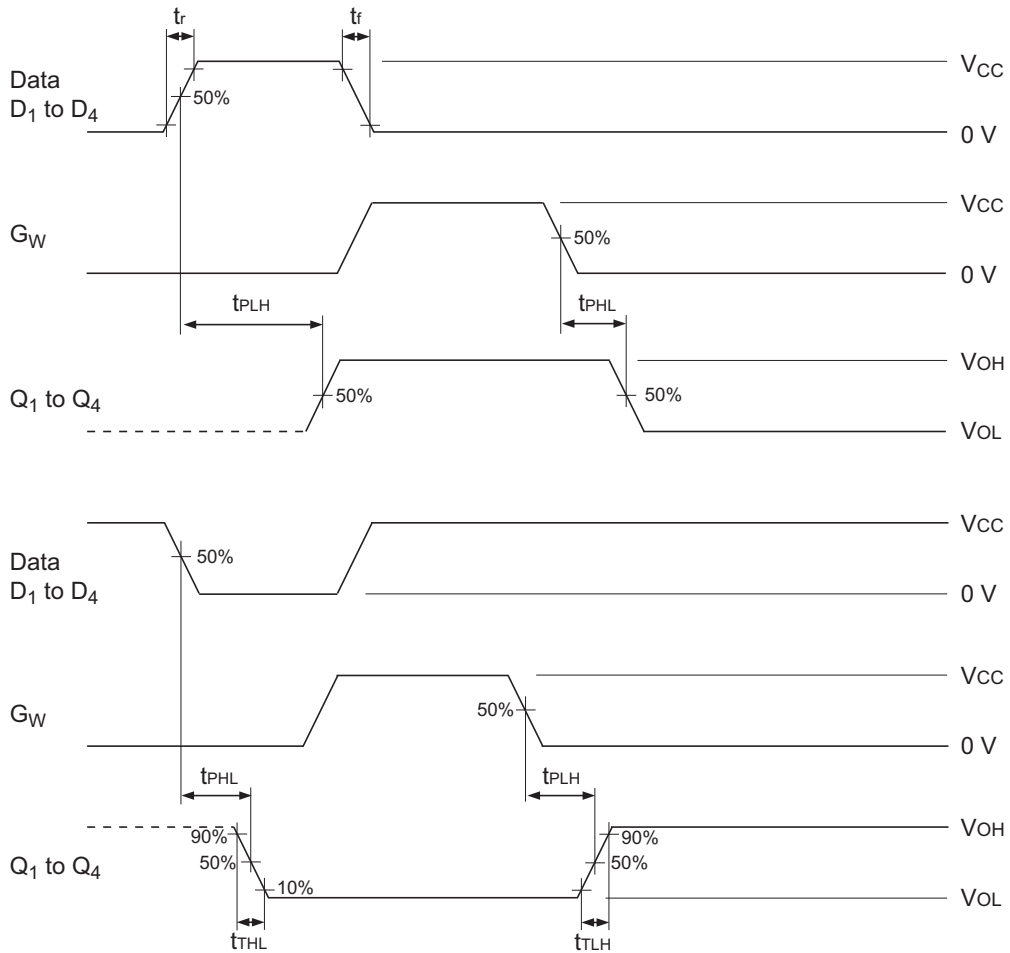
Test Circuit



Waveforms

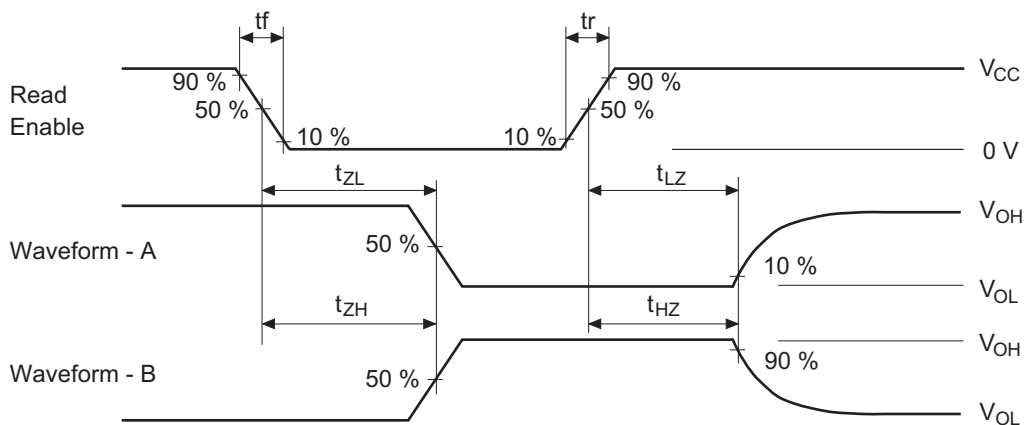


• Waveform – 2



Note : 1. Input waveform : PRR ≤ 1 MHz, duty cycle 50%,  $t_r \leq 6$  ns,  $t_f \leq 6$  ns

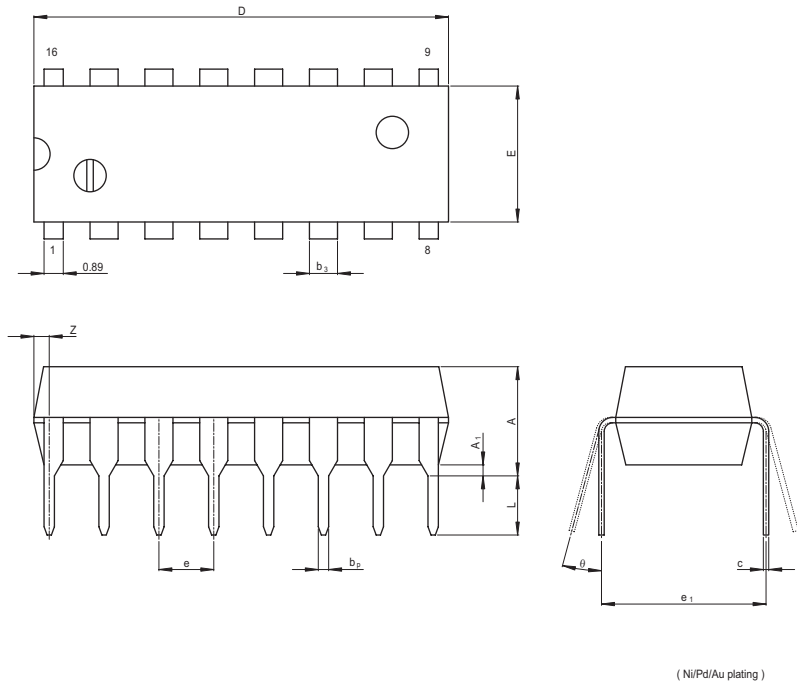
• Waveform – 3



- Notes : 1. Input waveform : PRR ≤ 1 MHz, duty cycle 50%,  $t_r \leq 6$  ns,  $t_f \leq 6$  ns
- 2. Waveform - A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform - B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

Package Dimensions

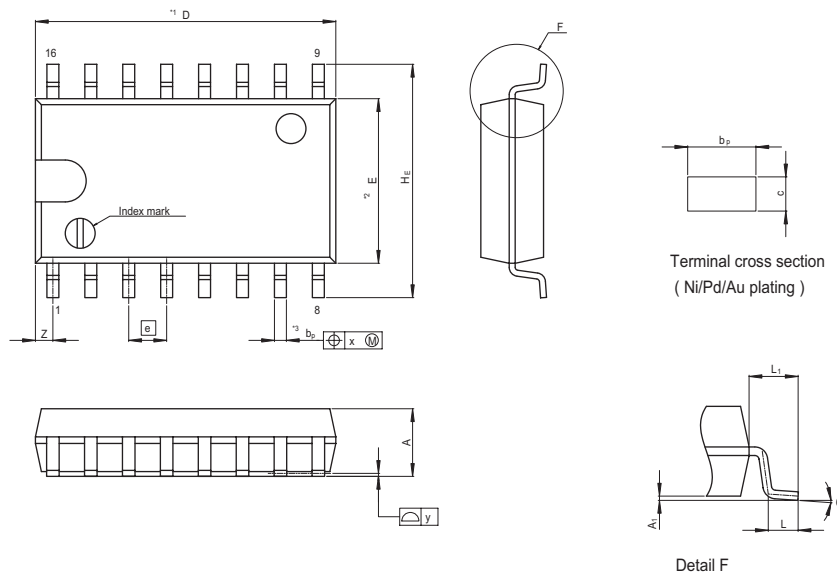
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-DIP16-6.3x19.2-2.54	PRDP0016AE-B	DP-16FV	1.05g



Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
e <sub>1</sub>	—	7.62	—
D	—	19.2	20.32
E	—	6.3	7.4
A	—	—	5.06
A <sub>1</sub>	0.51	—	—
b <sub>p</sub>	0.40	0.48	0.56
b <sub>3</sub>	—	1.30	—
c	0.19	0.25	0.31
θ	0°	—	15°
e	2.29	2.54	2.79
Z	—	—	1.12
L	2.54	—	—

( Ni/Pd/Au plating )

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-SOP16-5.5x10.06-1.27	PRSP0016DH-B	FP-16DAV	0.24g



NOTE  
 1. DIMENSIONS\*\*1 (Nom)\*\*AND\*\*2\* DO NOT INCLUDE MOLD FLASH.  
 2. DIMENSION\*\*3\*DOES NOT INCLUDE TRIM OFFSET.

Terminal cross section  
( Ni/Pd/Au plating )

Detail F

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	10.06	10.5
E	—	5.50	—
A <sub>2</sub>	—	—	—
A <sub>1</sub>	0.00	0.10	0.20
A	—	—	2.20
b <sub>p</sub>	0.34	0.40	0.46
b <sub>1</sub>	—	—	—
c	0.15	0.20	0.25
c <sub>1</sub>	—	—	—
θ	0°	—	8°
HE	7.50	7.80	8.00
ⓐ	—	1.27	—
x	—	—	0.12
y	—	—	0.15
Z	—	—	0.80
L	0.50	0.70	0.90
L <sub>1</sub>	—	1.15	—



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